

Session Program

16-18 Oct 2006

9th RD50 Workshop

***Pad Detector Characterization & Material
Engineering***

CERN, 40-SS-C01

Monday 16 October

11:25

Pad Detector Characterization & Material Engineering

Session | Location: CERN, 40-SS-C01

11:25-11:45 **DC bias effects in CV measurements**

Speaker

Alexander Chilingarov

11:45-12:05

Effect of bias voltage on full depletion voltage measured for different materials

Speaker

Gregor Kramberger

12:05-13:30 **Lunch break**

13:30-13:50 **Neutron irradiation effects in epitaxial silicon detectors**

Speaker

Vladimir Khomenkov

13:50-14:10

Recent results of measurements performed on irradiated epitaxial and MCz silicon devices of the SMART Collaboration

Speaker

Anna Macchiolo

14:10-14:30 **Homogeneity and thermal donors in p-type MCz-Si detector materials**

Speaker

Panja Luukka

14:30-14:50

CCE and CV/IV measurements and annealing studies with irradiated p-type MCz diodes

Speaker

Herbert Hoedlmoser

14:50-15:10

Charge collection in p- and n-type MCz Si microstrip and single pad SMART detectors irradiated with 26MeV protons

Speaker

Monica Scaringella

15:10-15:40 **Coffee Break**

15:40-16:00 **Modeling Radiation Damage Effects in Oxygenated Silicon Detectors**

Speaker

Marco Petasecca

16:00-16:20 **Electric field distribution in irradiated MCZ Si detectors**

Speaker

Elena Verbitskaya

16:20-16:40

Recent results on electric field distribution in SMART irradiated detectors on MCZ and epitaxial silicon

Speaker

Vladimir Eremin

16:40-17:00

Measurements of Lorentz angle in irradiated silicon strip sensors

Speaker

Michael Krause

17:00-17:30

Discussion Session (Pad Detector Characterization & Material Engineering)

Speakers

Eckhart Fretwurst, Gregor Kramberger

17:30